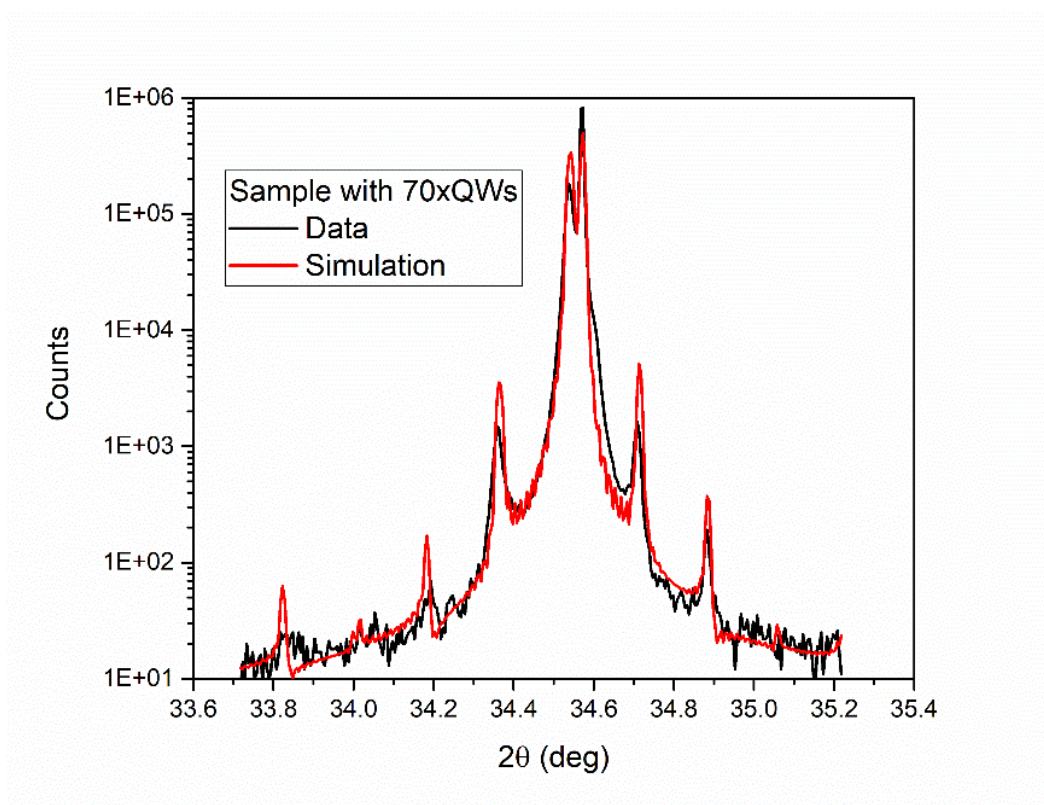


XRD measurement of sample with 70xQWs

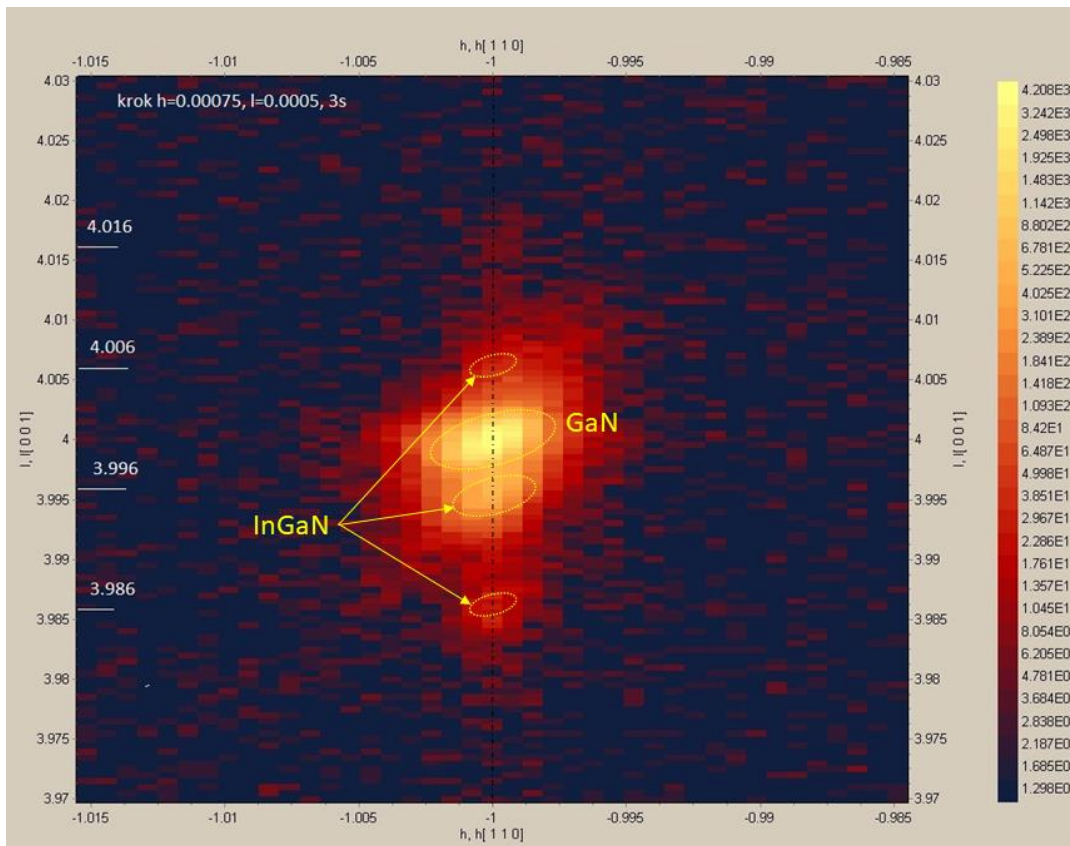
1) 2theta-omega scan of symmetric diffraction (002)



- Simulation results:
 - Periodicity = 6.65 nm
 - GaN thickness = 5 nm
 - InGaN thickness = 1.65 nm
 - $\text{In}_x\text{Ga}_{1-x}\text{N}$ composition: $x = 3.8\%$

2) Reciprocal space map (RSM) of asymmetric diffraction (-114)

- GaN and InGaN peaks are vertically correlated (InGaN is fully strained to GaN buffer)
- No relaxation was observed



- L scan with 3 different configurations, position of InGaN peaks are marked similarly to RSM

